







SN74AVCH8T245 SCES565I - APRIL 2004 - REVISED NOVEMBER 2023

SN74AVCH8T245 8-Bit Dual-Supply Bus Transceiver With Configurable Level-Shifting, Voltage Translation, and 3-State Outputs

1 Features

- Control inputs (DIR and \overline{OE}) V_{IH} and V_{IL} levels are referenced to V_{CCA} voltage
- Bus hold on data inputs eliminates the need for external pullup or pulldown resistors
- V_{CC} isolation feature
- Fully configurable dual-rail design
- I/Os are 4.6-V tolerant
- I_{off} supports partial-power-down mode operation
- Maximum data rates:
 - 320 Mbps (V_{CCA} ≥ 1.8 V and V_{CCB} ≥ 1.8 V)
 - 170 Mbps (V_{CCA} ≤ 1.8 V or V_{CCB} ≤ 1.8 V)
- Latch-up performance exceeds 100 mA per JESD 78. class II
- ESD protection exceeds JESD 22:
 - 8000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

2 Applications

- Personal electronics
- Industrial
- **Enterprise**
- **Telecommunications**

3 Description

The SN74AVCH8T245 is an 8-bit noninverting bus transceiver that uses two separate configurable power-supply rails. The A port is designed to track V_{CCA}, which accepts any supply voltage from 1.2 V to 3.6 V. The B port is designed to track V_{CCB}, which also accepts any supply voltage from 1.2 V to 3.6 V. This allows for universal low-voltage bidirectional translation between any of the 1.2-V, 1.5-V, 1.8-V, 2.5-V, and 3.3-V voltage nodes.

The SN74AVCH8T245 is designed for asynchronous communication between data buses. The device transmits data from either the A bus to the B bus, or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The outputenable (OE) input can be used to disable the outputs so the buses are effectively isolated.

The design of SN74AVCH8T245 references the control pins (DIR and \overline{OE}) to V_{CCA} .

Active bus-hold circuitry holds unused or undriven inputs at a valid logic state. It is not recommended to use pullup or pulldown resistors with the bus-hold circuitry.

This device is fully specified for partial-power-down applications using Ioff. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device.

The V_{CC} isolation feature allows the outputs to be in the high-impedance state when either V_{CCA} or V_{CCB} is at GND. The bus-hold circuitry on the powered-up side always stays active.

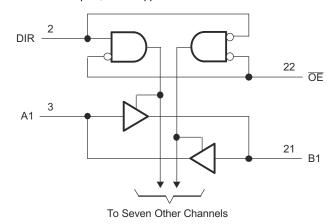
The SN74AVCH8T245 solution is compatible with a single-supply system and can be replaced later with a '245 function, with minimal printed circuit board redesign.

To put the device in the high-impedance state during power up or power down, \overline{OE} must be tied to V_{CCA} through a pullup resistor; the current-sinking capability of the driver determines the minimum value of the resistor.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE(2)		
	DGV (TVSOP, 24)	5 mm × 6.4 mm		
SN74AVCH8T245	PW (TSSOP, 24)	7.8 mm × 6.4 mm		
	RHL (VQFN, 24)	5.5 mm × 3.5 mm		

- For more information, see Section 11.
- The package size (length × width) is a nominal value and includes pins, where applicable.



Logic Diagram (Positive Logic)



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4 Pin Configuration and Functions

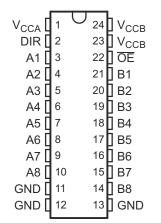


Figure 4-1. DGV or PW Package, 24-Pin TVSOP or TSSOP (Top View)

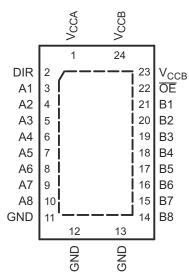


Figure 4-2. RHL Package, 24-Pin VQFN (Top View)

Table 4-1. Pin Functions

	PIN	I/O	DESCRIPTION
NAME	NO.	1/0	DESCRIPTION
A1	3	I/O	Input/output A1. Referenced to V _{CCA} .
A2	4	I/O	Input/output A2. Referenced to V _{CCA} .
A3	5	I/O	Input/output A3. Referenced to V _{CCA} .
A4	6	I/O	Input/output A4. Referenced to V _{CCA} .
A5	7	I/O	Input/output A5. Referenced to V _{CCA} .
A6	8	I/O	Input/output A6. Referenced to V _{CCA} .
A7	9	I/O	Input/output A7. Referenced to V _{CCA} .
A8	10	I/O	Input/output A8. Referenced to V _{CCA} .
B1	21	I/O	Input/output B1. Referenced to V _{CCB} .
B2	20	I/O	Input/output B2. Referenced to V _{CCB} .
В3	19	I/O	Input/output B3. Referenced to V _{CCB} .
B4	18	I/O	Input/output B4. Referenced to V _{CCB} .
B5	17	I/O	Input/output B5. Referenced to V _{CCB} .
B6	16	I/O	Input/output B6. Referenced to V _{CCB} .
B7	15	I/O	Input/output B7. Referenced to V _{CCB} .
B8	14	I/O	Input/output B8. Referenced to V _{CCB} .
DIR	2	I	Direction-control signal. Referenced to V _{CCA} .
GND	11, 12, 13	_	Ground
ŌĒ	22	I	3-state output-mode enables. Pull $\overline{\text{OE}}$ high to place all outputs in 3-state mode. Referenced to V _{CCA} .
V _{CCA}	1	_	A-port supply voltage. 1.2 V ≤ V _{CCA} ≤ 3.6 V
V _{CCB}	23, 24	_	B-port supply voltage. 1.2 V ≤ V _{CCA} ≤ 3.6 V



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

·		,	MIN	MAX	UNIT
V _{CCA}	Supply voltage		-0.5	4.6	V
V CCB		I/O ports (A port)	-0.5	4.6	
		_ ` ` ` '			
VI	Input voltage ⁽²⁾	I/O ports (B port)	-0.5	4.6	V
		Control inputs	-0.5	4.6	
.,	Voltage applied to any output	A port	-0.5	4.6	V
Vo	in the high-impedance or power-off state ⁽²⁾	B port	-0.5	4.6	V
V	Voltage applied to any output in the high or law state(2) (3)	A port	-0.5	V _{CCA} + 0.5	V
Vo	Voltage applied to any output in the high or low state ^{(2) (3)}	B port	-0.5	V _{CCB} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		– 50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current	•		±50	mA
	Continuous current through V _{CCA} , V _{CCB} , or GND			±100	mA
TJ	Junction temperature		-40	150	°C
T _{stg}	Storage temperature		-65	150	°C

Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- The output positive-voltage rating may be exceeded up to 4.6 V maximum if the output current rating is observed.
- The package thermal impedance is calculated in accordance with JESD 51-7.

5.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±8000	
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V
		Machine model (MM)	±200	

Product Folder Links: SN74AVCH8T245

- JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

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5.3 Recommended Operating Conditions

See (1) (2)

				MIN	MAX	UNIT	
V _{CCA}	Supply voltage			1.2	3.6	V	
V _{CCB}	Supply voltage			1.2	3.6	V	
			V _{CCI} = 1.2 V to 1.95 V	V _{CCI} × 0.65			
V_{IH}	High-level input voltage(1)	Data inputs	V _{CCI} = 1.95 V to 2.7 V	1.6		V	
			V _{CCI} = 2.7 V to 3.6 V	2			
			V _{CCI} = 1.2 V to 1.95 V		V _{CCI} × 0.35		
V_{IL}	Low-level input voltage ⁽¹⁾	Data inputs	V _{CCI} = 1.95 V to 2.7 V		0.7	V	
			V _{CCI} = 2.7 V to 3.6 V		0.8		
		DID 1 0=	V _{CCI} = 1.2 V to 1.95 V	V _{CCA} × 0.65			
V_{IH}	High-level input voltage	DIR and OE (referenced to V _{CCA})	V _{CCI} = 1.95 V to 2.7 V	1.6		V	
		(Colorelled to TCCA)	V _{CCI} = 2.7 V to 3.6 V	2			
		DID 105	V _{CCI} = 1.2 V to 1.95 V		V _{CCA} × 0.35		
V_{IL}	Low-level input voltage	DIR and OE (referenced to V _{CCA})	V _{CCI} = 1.95 V to 2.7 V		0.7	V	
		(referenced to v _{CCA})	V _{CCI} = 2.7 V to 3.6 V		0.8		
VI	Input voltage	Control Inputs	·	0	3.6	V	
\/	Output voltage ⁽²⁾	Active state		0	V _{cco}	V	
Vo	Output voltage 47	3-state	3-state		3.6	V	
			V _{CCO} = 1.2 V		-3		
			V _{CCO} = 1.4 V to 1.6 V		-6		
I _{OH}	High-level output current		V _{CCO} = 1.65 V to 1.95 V		-8	mA	
			$V_{CCO} = 2.3 \text{ V to } 2.7 \text{ V}$		-9		
			$V_{CCO} = 3 \text{ V to } 3.6 \text{ V}$		-12		
			V _{CCO} = 1.2 V		3		
			V _{CCO} = 1.4 V to 1.6 V		6		
I_{OL}	Low-level output current		V _{CCO} = 1.65 V to 1.95 V		8	8 mA	
			V _{CCO} = 2.3 V to 2.7 V		9		
	V _{CCO} = 3 V to 3.6 V				12		
Δt/Δν	Input transition rise or fall rate				5	ns/V	
T _A	Operating free-air temperature	e		-40	85	°C	

 $[\]begin{array}{ll} \hbox{(1)} & V_{CCI} \text{ is the } V_{CC} \text{ associated with the input port.} \\ \hbox{(2)} & V_{CCO} \text{ is the } V_{CC} \text{ associated with the output port.} \\ \end{array}$



5.4 Thermal Information

		:	SN74AVCH8T245	i	
	THERMAL METRIC ⁽¹⁾	DGV (TVSOP)	PW (TSSOP)	RHL (VQFN)	UNIT
		24 PINS	24 PINS	24 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽⁴⁾	116.7	93.1	36.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	48.5	36.7	32.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	62.1	48.4	15.7	°C/W
ΨЈТ	Junction-to-top characterization parameter	7.0	93.1	0.7	°C/W
ΨЈВ	Junction-to-board characterization parameter	61.6	48.0	15.6	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	5.6	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

5.5 Electrical Characteristics

All typical limits apply over $T_A = 25^{\circ}C$, and all maximum and minimum limits apply over $T_A = -40^{\circ}C$ to $85^{\circ}C$ (unless otherwise noted)

	PARAMETER	TEST	CONDITIONS	MIN	TYP	MAX	UNIT
		I _{OH} = -100 μA, V _I = V _{IH}	V _{CCA} = V _{CCB} = 1.2 V to 3.6 V	V _{CCO} - 0.2			
		$I_{OH} = -3 \text{ mA}, V_I = V_{IH}$	V _{CCA} = V _{CCB} = 1.2 V		0.95		
.,	High-level output	$I_{OH} = -6 \text{ mA}, V_I = V_{IH}$	V _{CCA} = V _{CCB} = 1.4 V	1.05			V
V _{OH}	voltage ⁽¹⁾	$I_{OH} = -8 \text{ mA}, V_I = V_{IH}$	V _{CCA} = V _{CCB} = 1.65 V	1.2			V
		I _{OH} = –9 mA, V _I = V _{IH}	V _{CCA} = V _{CCB} = 2.3 V	1.75			
		I _{OH} = -12 mA, V _I = V _{IH}	V _{CCA} = V _{CCB} = 3 V	2.3			
		I _{OL} = 100 μA, V _I = V _{IL}	V _{CCA} = V _{CCB} = 1.2 V to 3.6 V			0.2	
		I_{OL} = 3 mA, V_I = V_{IL}	V _{CCA} = V _{CCB} = 1.2 V		0.15		
.,	Low-level output	I _{OL} = 6 mA, V _I = V _{IL}	V _{CCA} = V _{CCB} = 1.4 V			0.35	V
V _{OL}	voltage	I _{OL} = 8 mA, V _I = V _{IL}	V _{CCA} = V _{CCB} = 1.65 V			0.45	V
		I _{OL} = 9 mA, V _I = V _{IL}	V _{CCA} = V _{CCB} = 2.3 V			0.55	
		I _{OL} = 12 mA, V _I = V _{IL}	V _{CCA} = V _{CCB} = 3 V			0.7	
I _I	Control inputs	V _I = V _{CCA} or GND	V _{CCA} = V _{CCB} = 1.2 V to 3.6 V		±0.025	±1	μΑ
		V _I = 0.42 V	V _{CCA} = V _{CCB} = 1.2 V		25		
	Bus-hold low	V _I = 0.49 V	V _{CCA} = V _{CCB} = 1.4 V	15			
I _{BHL}	sustaining	V _I = 0.58 V	V _{CCA} = V _{CCB} = 1.65 V	25			μΑ
	current ⁽⁵⁾	V _I = 0.7 V	V _{CCA} = V _{CCB} = 2.3 V	45			
		V _I = 0.8 V	V _{CCA} = V _{CCB} = 3.3 V	100			
		V _I = 0.78 V	V _{CCA} = V _{CCB} = 1.2 V		-25		
	Bus-hold high	V _I = 0.91 V	V _{CCA} = V _{CCB} = 1.4 V	-15			
I _{внн}	sustaining	V _I = 1.07 V	V _{CCA} = V _{CCB} = 1.65 V	-25			μΑ
	current ⁽⁶⁾	V _I = 1.6 V	V _{CCA} = V _{CCB} = 2.3 V	-45			
		V _I = 2 V	V _{CCA} = V _{CCB} = 3.3 V	-100			
			V _{CCA} = V _{CCB} = 1.2 V		50		
			V _{CCA} = V _{CCB} = 1.6 V	125			
I _{BHLO}	Bus-hold low overdrive current ⁽³⁾	$V_I = 0$ to V_{CC}	V _{CCA} = V _{CCB} = 1.95 V	200			μΑ
	Overdrive durient		$V_{CCA} = V_{CCB} = 2.7 \text{ V}$	300			
			V _{CCA} = V _{CCB} = 3.6 V	500			

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5.5 Electrical Characteristics (continued)

All typical limits apply over $T_A = 25$ °C, and all maximum and minimum limits apply over $T_A = -40$ °C to 85°C (unless otherwise noted)

	PARAMETER	TEST C	ONDITIONS		MIN	TYP	MAX	UNIT
			V _{CCA} = V _{CCB} = 1.2 V			-50		
			V _{CCA} = V _{CCB} = 1.6 V		-125			
I_{BHHO}	Bus-hold high overdrive current ⁽⁴⁾	$V_I = 0$ to V_{CC}	V _{CCA} = V _{CCB} = 1.95 V		-200			μΑ
	0.0.0		$V_{CCA} = V_{CCB} = 2.7 \text{ V}$		-300			
			$V_{CCA} = V_{CCB} = 3.6 \text{ V}$		-500			
1	Input/output power-off leakage	V _I = 0 V to 3.6 V,	$V_{CCA} = 0 \text{ V},$ $V_{CCB} = 0 \text{ V to } 3.6 \text{ V}$	A Port		±0.1	±5	μA
I _{off}	current	V _O = 0 V to 3.6 V	$V_{CCA} = 0 \text{ V to } 3.6 \text{ V},$ $V_{CCB} = 0 \text{ V}$	B Port		±0.1	±5	μΑ
		$V_O = V_{CCO}$ or GND, $V_I = V_{CCI}$ or GND, $\overline{OE} = V_{IH}$	V _{CCA} = V _{CCB} = 3.6 V	A Port, B Port		±0.5	±5	
l _{OZ}	Off-state output current (1) (2) (7)		V _{CCA} = 0 V, V _{CCB} = 3.6 V	B Port			±5	μΑ
			V _{CCA} = 3.6 V, V _{CCB} = 0 V	A Port			±5	
			V _{CCA} = V _{CCB} = 1.2 V to	o 3.6 V			8	
I_{CCA}	Supply current A port ⁽²⁾	$V_I = V_{CCI}$ or GND, $I_O = 0$	V _{CCA} = 0 V, V _{CCB} = 3.6 V				-2	μΑ
	F		V _{CCA} = 3.6 V, V _{CCB} = 0 V				8	
	0 b B		$V_{CCA} = V_{CCB} = 1.2 \text{ V to}$	o 3.6 V			8	
I_{CCB}	Supply current B port ⁽²⁾	$V_I = V_{CCI}$ or GND, $I_O = 0$	$V_{CCA} = 0 \text{ V}, V_{CCB} = 3.6$	6 V			8	μΑ
	•		$V_{CCA} = 3.6 \text{ V}, V_{CCB} = 0$	O V			-2	
I _{CCA} + I _{CCB}	Combined supply current ⁽²⁾	$V_I = V_{CCI}$ or GND, $I_O = 0$	$V_{CCA} = V_{CCB} = 1.2 \text{ V to}$	o 3.6 V			16	μΑ
Ci	Input capacitance control pins	V _I = 3.3 V or GND	$V_{CCA} = V_{CCB} = 3.3 \text{ V}$			3.5	4.5	pF
C _{io}	Input/output capacitance a or b port	V _O = 3.3 V or GND	V _{CCA} = V _{CCB} = 3.3 V			6	7	pF

- V_{CCO} is the V_{CC} associated with the output port. V_{CCI} is the V_{CC} associated with the input port.
- (2)
- (3) An external driver must source at least I_{BHLO} to switch this node from low to high.
- An external driver must sink at least I_{BHHO} to switch this node from high to low. The bus-hold circuit can sink at least the minimum low sustaining current at V_{IL} max. I_{BHL} should be measured after lowering V_{IN} to GND and then raising it to $V_{\text{IL}}\ \text{max}.$
- The bus-hold circuit can source at least the minimum high sustaining current at V_{IH} min. I_{BHH} should be measured after raising V_{IN} to V_{CC} and then lowering it to V_{IH} min.
- (7) For I/O ports, the parameter I_{OZ} includes the input leakage current.



5.6 Switching Characteristics, $V_{CCA} = 1.2 V$

T_A= 25°C (see Figure 6-1)

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP	MAX	UNIT
				V _{CCB} = 1.2 V		3.1		
	Propagation delay time:			V _{CCB} = 1.5 V		2.6		
t _{PLH} , t _{PHL}	low-to-high-level output and	Α	В	V _{CCB} = 1.8 V		2.5		ns
PHL	high-to-low level output			V _{CCB} = 2.5 V		3		
				V _{CCB} = 3.3 V		3.5		
				V _{CCB} = 1.2 V		3.1		
	Propagation delay time:			V _{CCB} = 1.5 V		2.7		
t _{PLH} , t _{PHL}	low-to-high-level output and	В	Α	V _{CCB} = 1.8 V		2.5		ns
PHL	high-to-low level output			V _{CCB} = 2.5 V		2.4		
				V _{CCB} = 3.3 V		2.3		
				V _{CCB} = 1.2 V		5.3		
	Enable time:	ŌĒ	A	V _{CCB} = 1.5 V		5.3		ns
t _{PZH} , t _{PZL}	to high level and to low level			V _{CCB} = 1.8 V		5.3		
				V _{CCB} = 2.5 V		5.3		
				V _{CCB} = 3.3 V		5.3		
				V _{CCB} = 1.2 V		5.1		
	Enable time:			V _{CCB} = 1.5 V		4		ns
t _{PZH} , t _{PZL}	to high level and	ŌĒ	В	V _{CCB} = 1.8 V		3.5		
PZL	to low level			V _{CCB} = 2.5 V		3.2		
				V _{CCB} = 3.3 V		3.1		
				V _{CCB} = 1.2 V		4.8		
	Disable time:			V _{CCB} = 1.5 V		4.8		
t _{PHZ} ,	from high level and	ŌĒ	Α	V _{CCB} = 1.8 V		4.8		ns
PLZ	from low level			V _{CCB} = 2.5 V		4.8		
				V _{CCB} = 3.3 V		4.8		
				V _{CCB} = 1.2 V		4.7		ns
	Disable time:			V _{CCB} = 1.5 V		4		
PHZ,	from high level and	ŌĒ	В	V _{CCB} = 1.8 V		4.1		
PLZ	from low level			V _{CCB} = 2.5 V		4.3		
				V _{CCB} = 3.3 V		5.1		

5.7 Switching Characteristics, V_{CCA} = 1.5 V ± 0.1 V

All typical limits apply over T_A = 25°C, and all maximum and minimum limits apply over T_A = -40°C to 85°C (unless otherwise noted) (see Figure 6-1)

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
				V _{CCB} = 1.2 V		2.7			
	Propagation delay time:			V _{CCB} = 1.5 V	0.5		5.4		
t _{PLH} , t _{PHL}	low-to-high-level output and	low-to-high-level output and	Α	В	V _{CCB} = 1.8 V	0.5		4.6	ns
PHL	high-to-low level output			V _{CCB} = 2.5 V	0.5		4.9		
				V _{CCB} = 3.3 V	0.5		6.8		
				V _{CCB} = 1.2 V		2.6			
	Propagation delay time:			V _{CCB} = 1.5 V	0.5		5.4		
lpLH,	low-to-high-level output and	В	Α	V _{CCB} = 1.8 V	0.5		5.1	ns	
PHL	high-to-low level output			V _{CCB} = 2.5 V	0.5		4.7		
				V _{CCB} = 3.3 V	0.5		4.5		
				V _{CCB} = 1.2 V		3.7		8.7 8.7 ns 8.7 8.7	
t _{PZH} , t _{PZL}	Enable time: to high level and to low level	ŌĒ	A	V _{CCB} = 1.5 V	1.1		8.7		
				V _{CCB} = 1.8 V	1.1		8.7		
				V _{CCB} = 2.5 V	1.1		8.7		
				V _{CCB} = 3.3 V	1.1		8.7		
		ŌĒ		V _{CCB} = 1.2 V		4.8			
	Enable time:			V _{CCB} = 1.5 V	1.1		7.6	7.6 7.1 ns 5.6 5.2	
PZH, PZL	to high level and		В	V _{CCB} = 1.8 V	1.1	-	7.1		
PZL	to low level			V _{CCB} = 2.5 V	1.1		5.6		
				V _{CCB} = 3.3 V	1.1		5.2		
				V _{CCB} = 1.2 V		3.1			
	Disable time:			V _{CCB} = 1.5 V	0.5		8.6		
t _{PHZ} , t _{PLZ}	from high level and	ŌĒ	Α	V _{CCB} = 1.8 V	0.5		8.6	ns	
-FLZ	from low level			V _{CCB} = 2.5 V	0.5		8.6		
				V _{CCB} = 3.3 V	0.5		8.6		
				V _{CCB} = 1.2 V		4.1			
	Disable time:		Ē B	V _{CCB} = 1.5 V	0.5		8.4		
PHZ,	from high level and from low level	nd <u>OE</u>		V _{CCB} = 1.8 V	0.5		7.6		
FLZ		from low level			V _{CCB} = 2.5 V	0.5		7.2	2
				V _{CCB} = 3.3 V	0.5		7.8		



5.8 Switching Characteristics, V_{CCA} = 1.8 V \pm 0.15 V

All typical limits apply over $T_A = 25^{\circ}C$, and all maximum and minimum limits apply over $T_A = -40^{\circ}C$ to $85^{\circ}C$ (unless otherwise noted) (see Figure 6-1)

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP	MAX	UNIT
				V _{CCB} = 1.2 V		2.5		
	Propagation delay time:	A	В	V _{CCB} = 1.5 V	0.5		5.1	
t _{PLH} , t _{PHL}	low-to-high-level output and			V _{CCB} = 1.8 V	0.5		4.4	ns
PHL	high-to-low level output			V _{CCB} = 2.5 V	0.5		4	
				V _{CCB} = 3.3 V	0.5		3.9	
				V _{CCB} = 1.2 V		2.5		
	Propagation delay time:			V _{CCB} = 1.5 V	0.5		4.6	
t _{PLH} , t _{PHL}	low-to-high-level output and	В	Α	V _{CCB} = 1.8 V	0.5		4.4	ns
PHL	high-to-low level output			V _{CCB} = 2.5 V	0.5		3.9	
				V _{CCB} = 3.3 V	0.5		3.7	
				V _{CCB} = 1.2 V		3		
	Enable time:			V _{CCB} = 1.5 V	1		6.8	
t _{PZH} , t _{PZL}	to high level and to low level	ŌĒ	A	V _{CCB} = 1.8 V	1		6.8	ns
				V _{CCB} = 2.5 V	1	,	6.8	
				V _{CCB} = 3.3 V	1		6.8	
				V _{CCB} = 1.2 V		4.6		
	Enable time:			V _{CCB} = 1.5 V	1.1		8.2	
t _{PZH} ,	to high level and	ŌĒ	В	V _{CCB} = 1.8 V	1	,	6.7	ns
t _{PZL}	to low level			V _{CCB} = 2.5 V	0.5	,	5.1	
				V _{CCB} = 3.3 V	0.5		4.5	
				V _{CCB} = 1.2 V		2.8		
	Disable time:			V _{CCB} = 1.5 V	0.5		7.1	
t _{PHZ} ,	from high level and	ŌĒ	Α	V _{CCB} = 1.8 V	0.5	,	7.1	ns
t _{PLZ}	from low level			V _{CCB} = 2.5 V	0.5		7.1	
				V _{CCB} = 3.3 V	0.5		7.1	
				V _{CCB} = 1.2 V		3.9		
	Disable time:			V _{CCB} = 1.5 V	0.5		7.8	
t _{PHZ} ,	from high level and	ŌĒ	В	V _{CCB} = 1.8 V	0.5		6.9	ns
t _{PLZ}	from low level				V _{CCB} = 2.5 V	0.5		6
				V _{CCB} = 3.3 V	0.5		5.8	

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5.9 Switching Characteristics, V_{CCA} = 2.5 V ± 0.2 V

All typical limits apply over T_A = 25°C, and all maximum and minimum limits apply over T_A = -40°C to 85°C (unless otherwise noted) (see Figure 6-1)

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
				V _{CCB} = 1.2 V		2.4			
	Propagation delay time:			V _{CCB} = 1.5 V	0.5		4.7		
t _{PLH} , t _{PHL}	low-to-high-level output and	Α	В	V _{CCB} = 1.8 V	0.5		3.9	ns	
PHL	high-to-low level output			V _{CCB} = 2.5 V	0.5		3.1		
				V _{CCB} = 3.3 V	0.5		2.8		
				V _{CCB} = 1.2 V		3			
	Propagation delay time:			V _{CCB} = 1.5 V	0.5		4.9		
t _{PLH} , t _{PHL}	low-to-high-level output and	В	Α	V _{CCB} = 1.8 V	0.5		4	ns	
PHL	high-to-low level output			V _{CCB} = 2.5 V	0.5		3.1		
				V _{CCB} = 3.3 V	0.5		2.9		
				V _{CCB} = 1.2 V		2.2		4	
	Enable time:		A	V _{CCB} = 1.5 V	0.5		4.8		
t _{PZH} , t _{PZL}	to high level and	ŌĒ		V _{CCB} = 1.8 V	0.5		4.8		
	to low level			V _{CCB} = 2.5 V	0.5		4.8		
				V _{CCB} = 3.3 V	0.5		4.8		
				V _{CCB} = 1.2 V		4.5			
	Enable time:		В	V _{CCB} = 1.5 V	1.1		7.9	ns	
PZH, PZL	to high level and	ŌĒ		V _{CCB} = 1.8 V	0.5	-	6.4		
PZL	to low level			V _{CCB} = 2.5 V	0.5		4.6		
				V _{CCB} = 3.3 V	0.5		4		
				V _{CCB} = 1.2 V		1.8			
	Disable time:			V _{CCB} = 1.5 V	0.5		5.1		
t _{PHZ} , t _{PLZ}	from high level and	ŌĒ	Α	V _{CCB} = 1.8 V	0.5		5.1	ns	
-FLZ	from low level			V _{CCB} = 2.5 V	0.5		5.1		
				V _{CCB} = 3.3 V	0.5		5.1		
				V _{CCB} = 1.2 V		3.6			
	Disable time:			V _{CCB} = 1.5 V	0.5		7.1	1	
PHZ [,]	from high level and	ŌĒ	В	V _{CCB} = 1.8 V	0.5		6.3	ns	
r LZ	from low level			V _{CCB} = 2.5 V	0.5		5.1		
				V _{CCB} = 3.3 V	0.5		3.9		



5.10 Switching Characteristics, V_{CCA} = 3.3 V \pm 0.3 V

All typical limits apply over $T_A = 25^{\circ}C$, and all maximum and minimum limits apply over $T_A = -40^{\circ}C$ to 85°C (unless otherwise noted) (see Figure 6-1)

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
				V _{CCB} = 1.2 V		2.3			
	Propagation delay time:			V _{CCB} = 1.5 V	0.5		4.5		
t _{PLH} , t _{PHL}	low-to-high-level output and	Α	В	V _{CCB} = 1.8 V	0.5		3.7	ns	
PHL	high-to-low level output			V _{CCB} = 2.5 V	0.5		2.9		
				V _{CCB} = 3.3 V	0.5		2.5		
				V _{CCB} = 1.2 V		3.5			
t _{PLH} , low-to-h	Propagation delay time:			V _{CCB} = 1.5 V	0.5		6.8		
	low-to-high-level output and	В	Α	V _{CCB} = 1.8 V	0.5	-	3.9	ns	
PUL	high-to-low level output			V _{CCB} = 2.5 V	0.5		2.8		
				V _{CCB} = 3.3 V	0.5		2.5		
				V _{CCB} = 1.2 V		2			
	Enable time:		A	V _{CCB} = 1.5 V	0.5		4	ns	
t _{PZH} , t _{PZL}	to high level and	ŌĒ		V _{CCB} = 1.8 V	0.5		4		
	to low level			V _{CCB} = 2.5 V	0.5		4		
				V _{CCB} = 3.3 V	0.5		4		
				V _{CCB} = 1.2 V		4.5			
	Enable time:			V _{CCB} = 1.5 V	1.1		7.8	ns	
l _{PZH} , l _{PZL}	to high level and	ŌĒ	В	V _{CCB} = 1.8 V	0.5	-	6.2		
-FZL	to low level			V _{CCB} = 2.5 V	0.5		4.5		
				V _{CCB} = 3.3 V	0.5		3.9		
				V _{CCB} = 1.2 V		1.7			
	Disable time:			V _{CCB} = 1.5 V	0.5		4		
t _{PHZ} , t _{PLZ}	from high level and	ŌĒ	Α	V _{CCB} = 1.8 V	0.5		4	ns	
-FLZ	from low level			V _{CCB} = 2.5 V	0.5		4		
				V _{CCB} = 3.3 V	0.5		4		
				V _{CCB} = 1.2 V		3.4			
	Disable time:			V _{CCB} = 1.5 V	0.5		6.9		
PHZ [,]	from high level and	ŌĒ	В	V _{CCB} = 1.8 V	0.5		6	ns	
FLZ	from low level			V _{CCB} = 2.5 V	0.5		4.8		
				V _{CCB} = 3.3 V	0.5		4.2		

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5.11 Operating Characteristics

T_A= 25°C

	PARAMETER	FROM (INPUT)	(OUTPUT)	TEST	CONDITIONS	TYP	UNIT	
					V _{CCA} = V _{CCB} = 1.2 V	1		
	Power dissipation capacitance			$C_1 = 0 pF$	V _{CCA} = V _{CCB} = 1.5 V	1		
	per transceiver ⁽¹⁾	Α	В	f = 10 MHz,	V _{CCA} = V _{CCB} = 1.8 V	1		
	port A - outputs enabled			$t_r = t_f = 1 \text{ ns}$	V _{CCA} = V _{CCB} = 2.5 V	1		
					V _{CCA} = V _{CCB} = 3.3 V	1		
					V _{CCA} = V _{CCB} = 1.2 V	1		
	Power dissipation capacitance			$C_1 = 0 pF$	V _{CCA} = V _{CCB} = 1.5 V	1		
	per transceiver ⁽¹⁾	Α	В	f = 10 MHz,	V _{CCA} = V _{CCB} = 1.8 V	1		
	port A - outputs disabled			$t_r = t_f = 1 \text{ ns}$	V _{CCA} = V _{CCB} = 2.5 V	1		
_					V _{CCA} = V _{CCB} = 3.3 V	1	pF	
C _{pdA}					V _{CCA} = V _{CCB} = 1.2 V	12	рг	
	Power dissipation capacitance			$C_1 = 0 pF$	V _{CCA} = V _{CCB} = 1.5 V	12		
	per transceiver ⁽¹⁾	В	Α	f = 10 MHz,	V _{CCA} = V _{CCB} = 1.8 V	12		
	port A - outputs enabled			$t_r = t_f = 1 \text{ ns}$	V _{CCA} = V _{CCB} = 2.5 V	13		
					V _{CCA} = V _{CCB} = 3.3 V	14		
					V _{CCA} = V _{CCB} = 1.2 V	1		
	Power dissipation capacitance			$C_L = 0 pF$	V _{CCA} = V _{CCB} = 1.5 V	1		
	per transceiver ⁽¹⁾	В	Α	f = 10 MHz,	V _{CCA} = V _{CCB} = 1.8 V	1		
	port A - outputs disabled			$t_r = t_f = 1 \text{ ns}$	V _{CCA} = V _{CCB} = 2.5 V	1		
					V _{CCA} = V _{CCB} = 3.3 V	1		
		A	В	$C_L = 0 \text{ pF},$ f = 10 MHz, $t_r = t_f = 1 \text{ ns}$	V _{CCA} = V _{CCB} = 1.2 V	12		
	Power dissipation capacitance				V _{CCA} = V _{CCB} = 1.5 V	12		
	per transceiver ⁽¹⁾				V _{CCA} = V _{CCB} = 1.8 V	12		
	port B - outputs enabled				V _{CCA} = V _{CCB} = 2.5 V	13		
					V _{CCA} = V _{CCB} = 3.3 V	14		
					V _{CCA} = V _{CCB} = 1.2 V	1		
	Power dissipation capacitance			$C_1 = 0 pF$	V _{CCA} = V _{CCB} = 1.5 V	1	1	
	per transceiver ⁽¹⁾	Α	В	f = 10 MHz,	V _{CCA} = V _{CCB} = 1.8 V	1		
	port B - outputs disabled			$t_r = t_f = 1 \text{ ns}$	V _{CCA} = V _{CCB} = 2.5 V	1		
_					V _{CCA} = V _{CCB} = 3.3 V	1		
S _{pdB}					V _{CCA} = V _{CCB} = 1.2 V	1	pF	
	Power dissipation capacitance			$C_1 = 0 pF$	V _{CCA} = V _{CCB} = 1.5 V	1		
	per transceiver ⁽¹⁾	В	Α	f = 10 MHz,	V _{CCA} = V _{CCB} = 1.8 V	1		
	port B - outputs enabled			$t_r = t_f = 1 \text{ ns}$	V _{CCA} = V _{CCB} = 2.5 V	1		
					V _{CCA} = V _{CCB} = 3.3 V	1		
					V _{CCA} = V _{CCB} = 1.2 V	1		
	Power dissipation capacitance			$C_1 = 0 pF$	V _{CCA} = V _{CCB} = 1.5 V	1		
	per transceiver ⁽¹⁾	В	Α	f = 10 MHz,	V _{CCA} = V _{CCB} = 1.8 V	1		
	port B - outputs disabled			$t_r = t_f = 1 \text{ ns}$	V _{CCA} = V _{CCB} = 2.5 V	1		
					V _{CCA} = V _{CCB} = 3.3 V	1		

⁽¹⁾ See to TI application report, CMOS Power Consumption and Cpd Calculation (SCAA035).



5.12 Typical Characteristics

 $T_A = 25^{\circ}C$

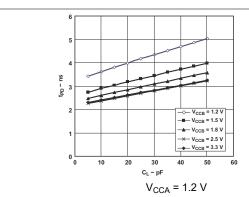


Figure 5-1. Typical Propagation Delay (A to B) vs Load Capacitance

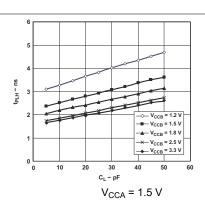


Figure 5-2. Typical Propagation Delay (A to B) vs Load Capacitance

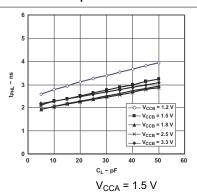


Figure 5-3. Typical Propagation Delay (A to B) vs Load Capacitance

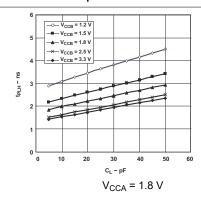


Figure 5-4. Typical Propagation Delay (A to B) vs Load Capacitance

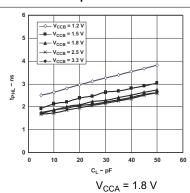


Figure 5-5. Typical Propagation Delay (A to B) vs Load Capacitance

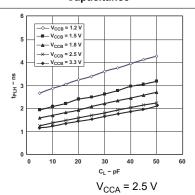
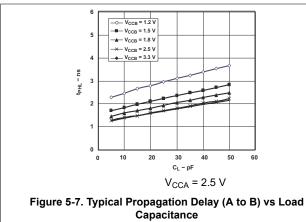


Figure 5-6. Typical Propagation Delay (A to B) vs Load Capacitance

5.12 Typical Characteristics (continued)

T_A = 25°C



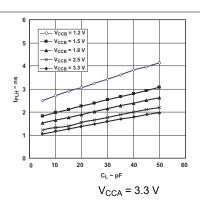


Figure 5-8. Typical Propagation Delay (A to B) vs Load Capacitance

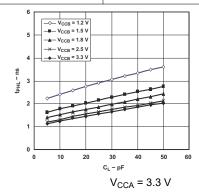
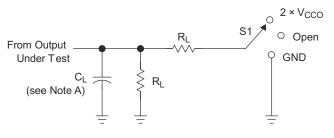


Figure 5-9. Typical Propagation Delay (A to B) vs Load Capacitance



 V_{CCA}

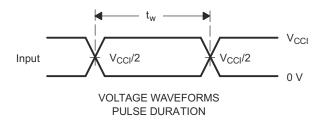
6 Parameter Measurement Information

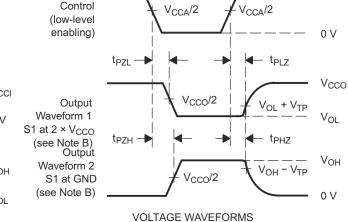


TEST	S1
t _{pd}	Open
t _{PLZ} /t _{PZL}	2 × V _{CCO}
t _{PHZ} /t _{PZH}	GND

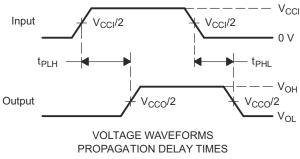
LOAD CIRCUIT

V _{CCO}	C _L	R _L	V _{TP}
1.2 V	15 pF	2 kW	0.1 V
1.5 V ± 0.1 V	15 pF	2 kW	0.1 V
1.8 V ± 0.15 V	15 pF	2 kW	0.15 V
2.5 V ± 0.2 V	15 pF	2 kW	0.15 V
3.3 V ± 0.3 V	15 pF	2 kW	0.3 V





ENABLE AND DISABLE TIMES



NOTES: A. C_L includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.

Output

- C. All input pulses are supplied by generators having the following characteristics: PRR 10 MHz, Z_O = 50 W, dv/dt ≥ 1 V/ns.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en} .
- $\begin{array}{ll} \text{G.} & t_{PLH} \text{ and } t_{PHL} \text{ are the same as } t_{pd}. \\ \text{H.} & V_{CCI} \text{ is the } V_{CC} \text{ associated with the input port.} \end{array}$
- I. V_{CCO} is the V_{CC} associated with the output port.

Figure 6-1. Load Circuit and Voltage Waveforms

7 Detailed Description

7.1 Overview

The SN74AVCH8T245 is an 8-bit, dual supply noninverting bidirectional voltage level translator. Pins A1 through A4, and the control pins (DIR and \overline{OE}) are referenced to V_{CCA} , while pins B1 through B4 are referenced to V_{CCB} . Both the A port and B port can accept I/O voltages ranging from 1.2 V to 3.6 V. With \overline{OE} set to low, a high on DIR allows data transmission from Port A to Port B, and a low on DIR allows data transmission from Port B to Port A. When \overline{OE} is set to high, both Port A and Port B outputs are in the high-impedance state. For more information, see *AVC Logic Family Technology and Application*.

7.2 Functional Block Diagram

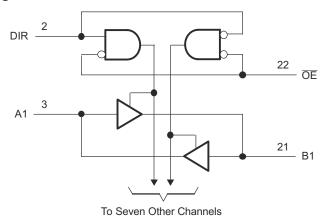


Figure 7-1. Logic Diagram (Positive Logic)

7.3 Feature Description

7.3.1 Fully Configurable Dual-Rail Design

Both V_{CCA} and V_{CCB} can be supplied at any voltage from 1.2 V to 3.6 V, making the device an excellent choice for translating between any of the low voltage nodes: 1.2 V, 1.8 V, 2.5 V, and 3.3 V.

Table : I Typical Total Calle : Constitution (ICCA ICCB)											
V	V _{CCA}										
V _{CCB}	0 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	UNIT				
0 V	0	<0.5	<0.5	<0.5	<0.5	<0.5					
1.2 V	<0.5	<1	<1	<1	<1	1					
1.5 V	<0.5	<1	<1	<1	<1	1					
1.8 V	<0.5	<1	<1	<1	<1	<1	μΑ				
2.5 V	<0.5	1	<1	<1	<1	<1					
3.3 V	<0.5	1	<1	<1	<1	<1					

Table 7-1. Typical Total Static Power Consumption (I_{CCA} + I_{CCB})

7.3.2 Supports High-Speed Translation

SN74AVCH8T245 can support high data rate applications, which can be calculated from the maximum propagation delay. This is also dependent on output load. The translated signal data rate can be up to 320 Mbps when both V_{CCA} and V_{CCB} are at least 1.8 V.

7.3.3 Partial-Power-Down Mode Operation

 I_{off} circuitry disables the outputs, preventing damaging current backflow through the SN74AVCH8T245 when it is powered down. Damaging current backflow can occur in applications where subsections of a system are powered down (partial-power-down) to reduce power consumption.



7.3.4 Bus-Hold Circuitry

Active bus-hold circuitry holds unused or undriven data inputs at a valid logic state, which helps with board space savings and reduced component costs. Use of pull-up or pull-down resistors with the bus-hold circuitry is not recommended. For more information, see *Bus-Hold Circuit*.

7.3.5 V_{CC} Isolation Feature

The V_{CC} isolation feature allows both ports to be in a high-impedance state if either V_{CCA} or V_{CCB} are at GND (or < 0.4 V). For more information, see I_{OZ} in the *Electrical Characteristics*. This feature prevents false logic levels from being presented to either bus.

7.4 Device Functional Modes

Table 7-2 lists the functional modes of the SN74AVCH8T245.

Table 7-2. Function Table (Each 8-Bit Section)

CONTROL	INPUTS ⁽¹⁾	OUTPUT	OPERATION		
ŌĒ	ŌĒ DIR		B PORT	OPERATION	
L	L	Enabled	Hi-Z	B data to A bus	
L	Н	Hi-Z	Enabled	A data to B bus	
Н	X	Hi-Z	Hi-Z	Isolation	

(1) Input circuits of the data I/Os are always active.

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8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The SN74AVCH8T245 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The SN74AVCH8T245 device is an excellent choice for data transmission when direction is different. The maximum data rate can be up to 320Mbps when device voltage power supply is more than 1.8 V.

8.2 Typical Application

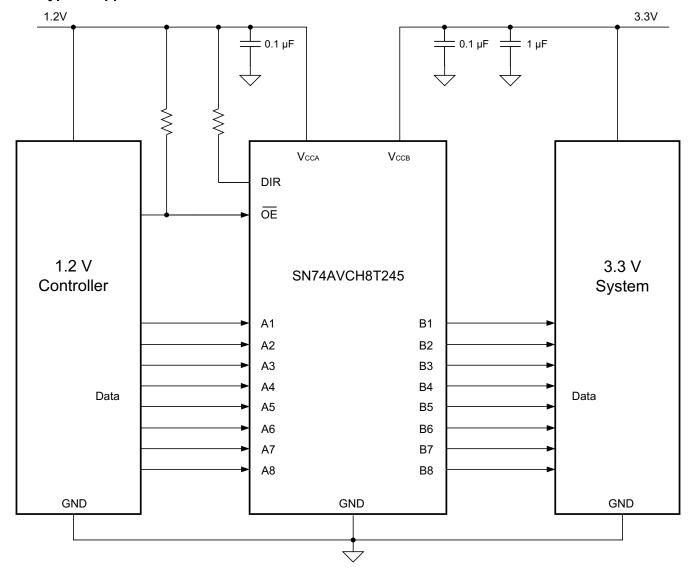


Figure 8-1. Typical Application Schematic

8.2.1 Design Requirements

For this design example, use the parameters listed in Table 8-1.

Table 8-1. Design Parameters

DESIGN PARAMETERS	EXAMPLE VALUE
Input voltage	1.2 V to 3.6 V
Output voltage	1.2 V to 3.6 V

8.2.2 Detailed Design Procedure

To begin the design process, determine the following:

- · Input voltage range:
 - Use the supply voltage of the device that is driving the SN74AVCH8T245 device to determine the input voltage range. For a valid logic high, the value must exceed the V_{IH} of the input port. For a valid logic low, the value must be less than the V_{IL} of the input port.
- Output voltage range:
 - Use the supply voltage of the device that the SN74AVCH8T245 device is driving to determine the output voltage range.

8.2.3 Application Curves

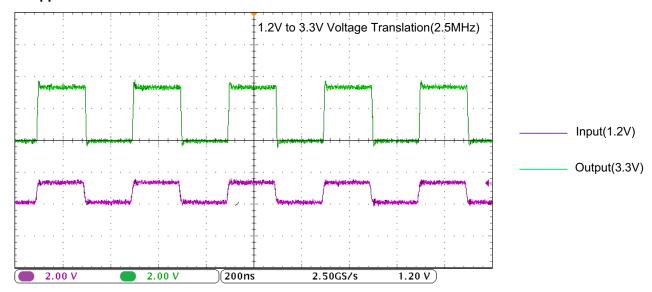


Figure 8-2. Translation Up (1.2 V to 3.3 V) at 2.5 MHz

8.3 Power Supply Recommendations

The design of the output-enable (\overline{OE}) input circuit is referenced to VCCA so that all outputs are placed in the high-impedance state when the \overline{OE} input is high. To put the outputs in a high-impedance state during power up or power down, the \overline{OE} input pin must be tied to V_{CCA} through a pullup resistor and must not be enabled until V_{CCA} and V_{CCB} are fully ramped and stable. The current-sinking capability of the driver determines the minimum value of the pullup resistor to V_{CCA} .

 V_{CCA} or V_{CCB} can be powered up first. If the SN74AVCH8T245 is powered up in a permanently enabled state (for example \overline{OE} is always kept low), then pullup resistors are recommended at the input. Doing this allows for proper, glitch-free, power-up. For more information, see *Designing with SN4LVCXT245 and SN74LVCHXT245 Family of Direction Controlled Voltage Translators/Level-Shifters*. In addition, the \overline{OE} pin may be shorted to GND if the application does not require use of the high-impedance state at any time.

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8.4 Layout

8.4.1 Layout Guidelines

For device reliability, TI recommends following the common printed-circuit board layout guidelines.

- Use bypass capacitors on power supplies.
- · Use short trace lengths to avoid excessive loading.
- Placing pads on the signal paths for loading capacitors or pullup resistors to help adjust rise and fall times of signals depending on the system requirements.

8.4.2 Layout Example



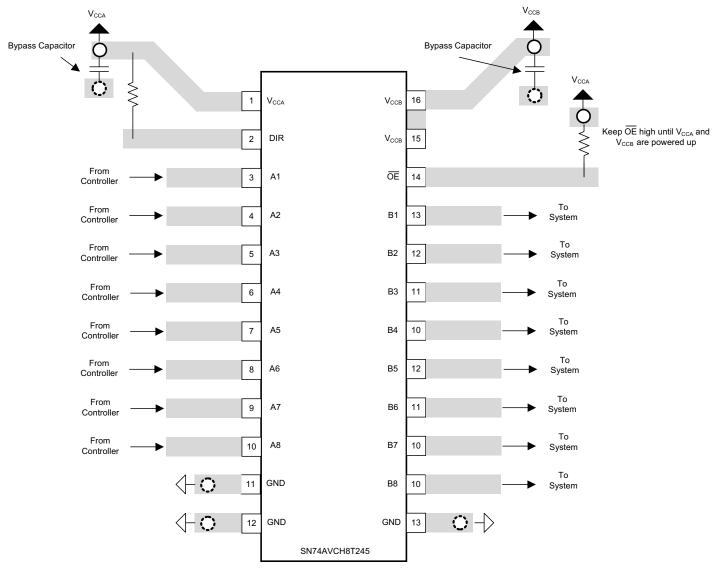


Figure 8-3. SN74AVCH8T245 Layout Example



9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, Designing with SN74LVCXT245 and SN74LVCHXT245 Family of Direction Controlled Voltage Translators/Level-Shifters
- Texas Instruments, Bus-Hold Circuit
- Texas Instruments, AVC Logic Family Technology and Applications
- Texas Instruments, CMOS Power Consumption and Cpd Calculation

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on Notifications to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

9.4 Trademarks

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9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision H (January 2016) to Revision I (November 2023)	Page
•	Updated the numbering format for tables, figures, and cross-references throughout the document	1
•	Updated the Package Information table to include package lead size	<u>1</u>
•	Updated the Thermal Information table for the DGV, PW, and RHL packages	6
С	hanges from Revision G (March 2007) to Revision H (January 2016)	Page
•	Added ESD Ratings table, Feature Description section, Device Functional Modes, Application and	
	Implementation section, Power Supply Recommendations section, Layout section, Device and	
	Documentation Support section, and Mechanical, Packaging, and Orderable Information section	1
•	Deleted the Ordering Information table	1

Submit Document Feedback Product Folder Links: SN74AVCH8T245



11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
74AVCH8T245PWRG4	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	(6) NIPDAU	Level-1-260C-UNLIM	-40 to 85	WP245	Samples
74AVCH8T245RHLRG4	ACTIVE	VQFN	RHL	24	1000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	WP245	Samples
SN74AVCH8T245DGVR	ACTIVE	TVSOP	DGV	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	WP245	Samples
SN74AVCH8T245PW	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	WP245	Samples
SN74AVCH8T245PWG4	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	WP245	Samples
SN74AVCH8T245PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	WP245	Samples
SN74AVCH8T245RHLR	ACTIVE	VQFN	RHL	24	1000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	WP245	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

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(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

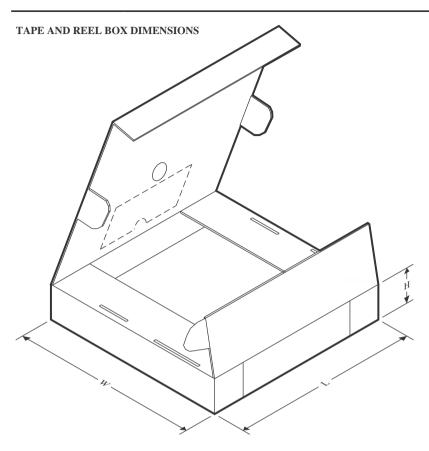


*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AVCH8T245DGVR	TVSOP	DGV	24	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74AVCH8T245PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
SN74AVCH8T245RHLR	VQFN	RHL	24	1000	180.0	12.4	3.8	5.8	1.2	8.0	12.0	Q1



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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins SPQ I		Length (mm)	Width (mm)	Height (mm)
SN74AVCH8T245DGVR	TVSOP	DGV	24	2000	356.0	356.0	35.0
SN74AVCH8T245PWR	TSSOP	PW	24	2000	356.0	356.0	35.0
SN74AVCH8T245RHLR	VQFN	RHL	24	1000	210.0	185.0	35.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN74AVCH8T245PW	PW	TSSOP	24	60	530	10.2	3600	3.5
SN74AVCH8T245PWG4	PW	TSSOP	24	60	530	10.2	3600	3.5

DGV (R-PDSO-G**)

24 PINS SHOWN

PLASTIC SMALL-OUTLINE



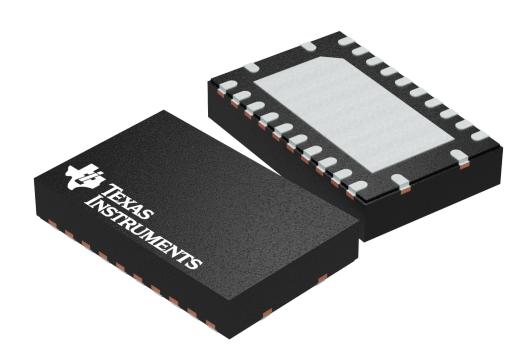
NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.

D. Falls within JEDEC: 24/48 Pins – MO-153 14/16/20/56 Pins – MO-194 5.5 x 3.5 mm, 0.5 mm pitch

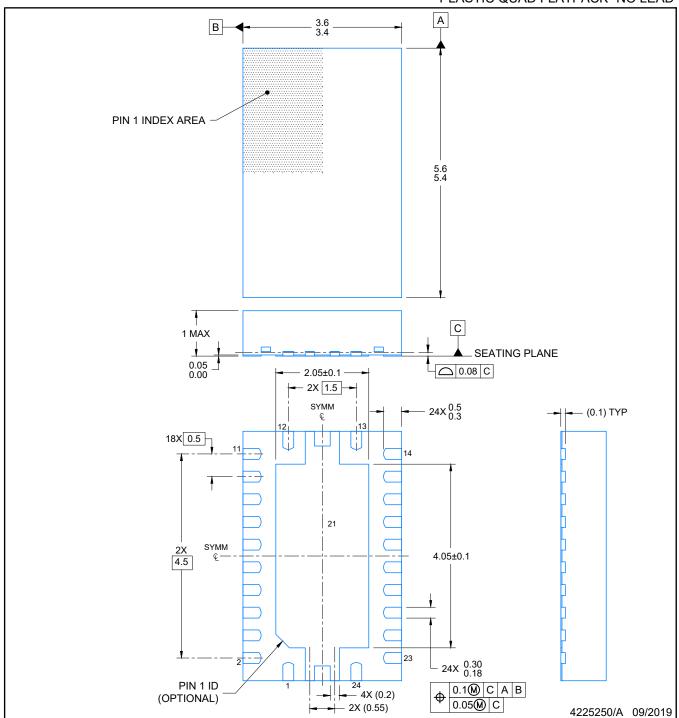
PLASTIC QUAD FLATPACK - NO LEAD



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



PLASTIC QUAD FLATPACK- NO LEAD

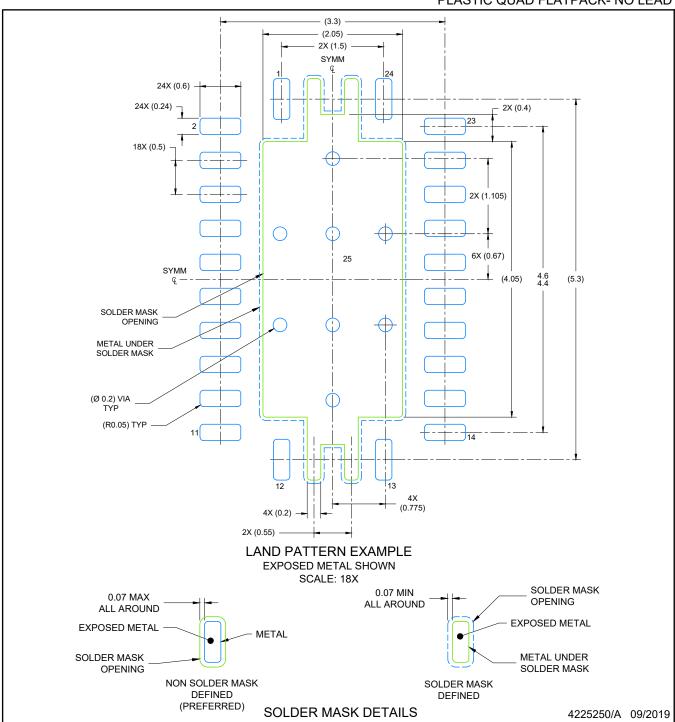


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



PLASTIC QUAD FLATPACK- NO LEAD

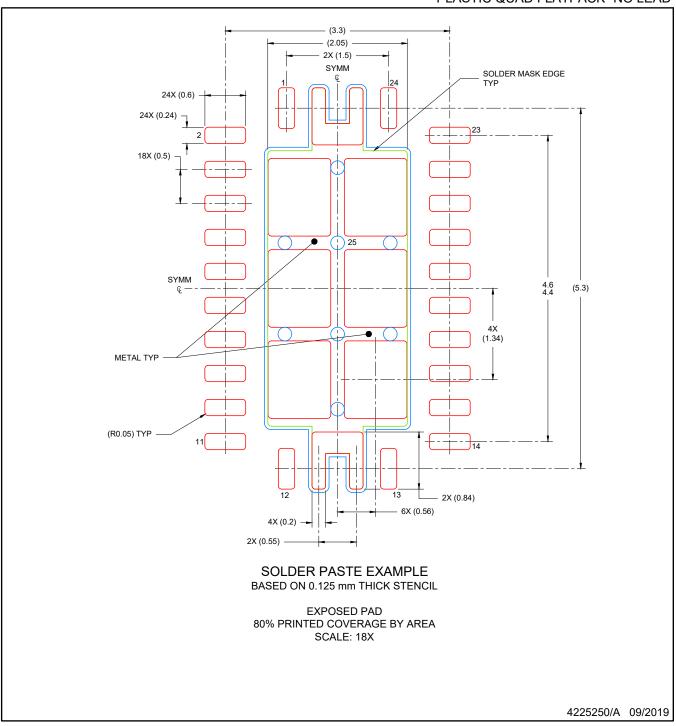


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK- NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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